

## Overview

The STK6855 is an H bridge power pack reversible brush-type DC motor driver that realizes low power dissipation, high efficiency, and large output currents by the adoption of MOSFET devices as the H bridge power elements. The servo control technique employed uses both an analog servo and a digital servo (software servo). Since the STK6855 uses a variable period (DC to 30 kHz) PWM signal in its rotation control technique, it is optimal for use as a driver in digital servo applications. Since the input block is LS-TTL level compatible, it can be directly connected to main control CPU and PLL control ICs. Furthermore, the only external component required is a power supply bypass capacitor.

## Applications

- Plain paper copier drum and scanner motors
- LBP drum motors
- Printer head carriage motors
- Industrial robot drive motors
- All types of DC motor application equipment

## Features

- Low power dissipation (only two-thirds that of the STK6860H series, which use bipolar transistors)

## Specifications

### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Condition	Rating	Unit
Maximum supply voltage 1	V <sub>CC1</sub> max	No signal	50	V
Maximum supply voltage 2	V <sub>CC2</sub> max	No signal	7	V
Maximum motor rush current	I <sub>O</sub> peak	Period = 100 msec, duty ≤ 1% When V <sub>CC2</sub> = 5.0 V	12	A
Operating case temperature	T <sub>c</sub> max		105	°C
Junction temperature	T <sub>j</sub> max		150	°C
Storage temperature	T <sub>stg</sub>		-40 to +125	°C

### Allowable Operating Ranges at Ta = 25°C

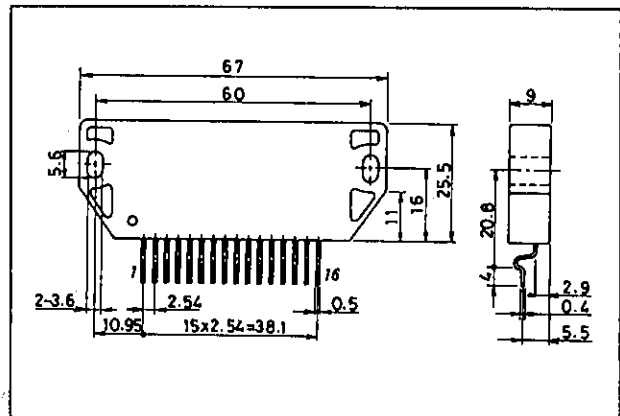
Parameter	Symbol	Condition	Rating	Unit
Supply voltage 1	V <sub>CC1</sub>	Input active	16 to 42	V
Supply voltage 2	V <sub>CC2</sub>	Input active	5 ±5%	V
Motor output current	I <sub>OH</sub> max	DC	5	A
PWM frequency	f <sub>p</sub>	Pin 14 input signal	0 to 30	kHz
FET withstand voltage	V <sub>DSS</sub> min		60	V
Input voltage	V <sub>IH</sub>	The input signal level for pins 13, 14 and 15	V <sub>CC2</sub>	V

- By independently extracting the signal line in PWM input handling, two pin low saturation operation is also possible with the PWM pin tied high.
- Few required external components. (Only a power supply bypass capacitor is required.)
- Wide operating power supply voltage range (V<sub>CC</sub> = 16 to 42 V)
- Inputs can handle LS-TTL level signals.
- A braking function is provided.

## Package Dimensions

unit: mm

4139



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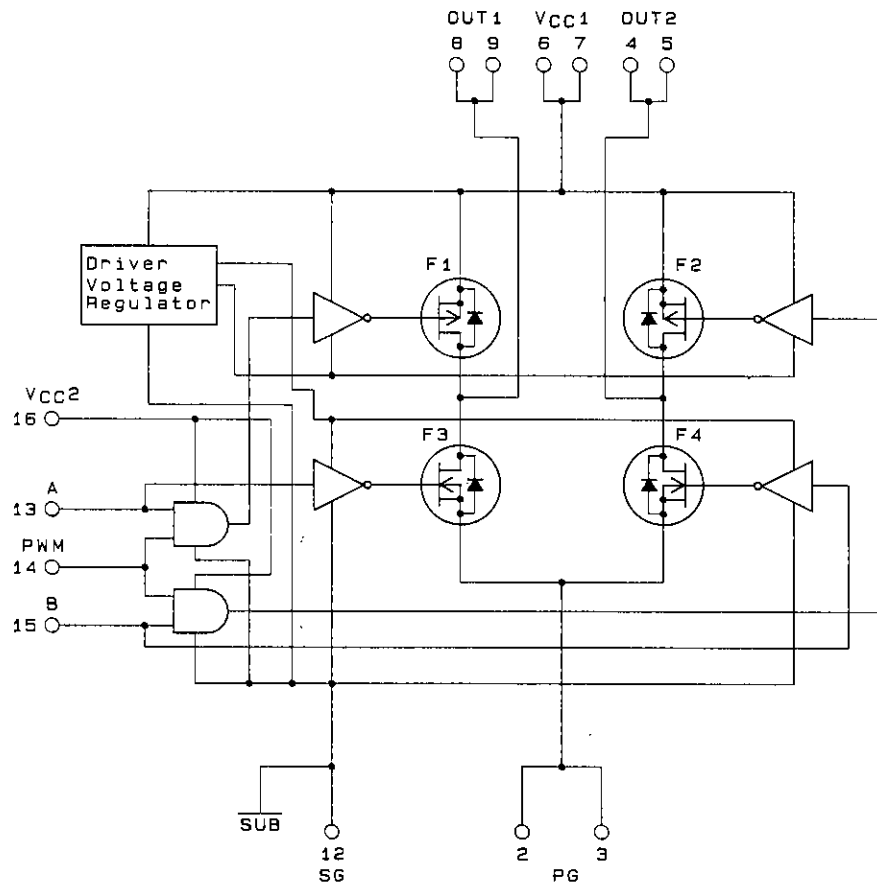
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Operating Characteristics at  $T_a = 25^\circ\text{C}$ ,  $V_{CC1} = 24\text{ V}$ ,  $V_{CC2} = 5.0\text{ V}$

Parameter	Symbol	Condition	Rating			Unit
			min	typ	max	
Quiescent current	$I_{CCO}$		12.0	13.5	15.0	mA
Output saturation voltage 1	$V_{st1}$	$R_L = 4.5\ \Omega$ (F3, F4)		0.85	1.2	V
Output saturation voltage 2	$V_{st2}$	$R_L = 4.5\ \Omega$ (F1, F2)		0.90	1.3	V
Input on voltage	$V_{IH}$	The input signal level for pins 13, 14 and 15	2.0		$V_{CC2}$	V
Input off voltage	$V_{IL}$	The input signal level for pins 13, 14 and 15	0		0.8	V
Input on current 1	$I_{IH1}$	$V_{IN} = 2.7\text{ V}$ , pin 14			20	$\mu\text{A}$
Input on current 2	$I_{IH2}$	$V_{IN} = 2.7\text{ V}$ , pin 13 or pin 15			20	$\mu\text{A}$
Input off current 1	$I_{IL1}$	$V_{IN} = 0.4\text{ V}$ , pin 14			-0.4	mA
Input off current 2	$I_{IL2}$	$V_{IN} = 0.4\text{ V}$ , pin 13 or pin 15			-0.6	mA
Diode forward voltage	$V_{df}$	$I_{df} = 5\text{ A}$ , $V_{GS} = 0$		1.3	1.8	V
Sensing voltage	$V_{sens}$	$V_{sens} (= PG)$			1.0	V

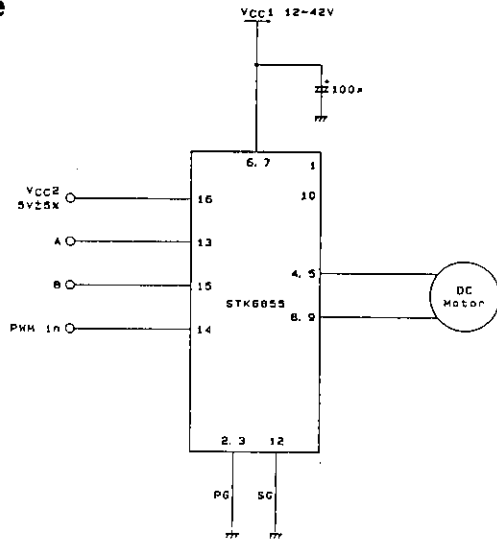
Note: Constant voltage power supplies must be used.

Equivalent Circuit



Note: Pins 1, 10 and 11 are NC (no connection) pins.

Application Circuit Example



	A	B
Forward	H	L
Reverse	L	H
Standby 1 (illegal)	H	H
Standby 2 (brake)	L	L

H: 5 V

L: 0 V

Note: Input pin specifications

- TTL levels handled
- Maximum PWM input frequency: 30 kHz
- When used in two pin control mode, the PWM pin must be tied high.

Thermal Design

1. Heat Sink Thermal Resistance ( $\theta_{c-a}$ ) Derivation

The size of the heat sink required for the hybrid IC is determined by the motor output current ( $I_{OH}$ ), the electrical characteristics of the motor and the chopping frequency, and the frequency of current application. The thermal resistance ( $\theta_{c-a}$ ) of the heat sink is derived from the following formula.

$$\theta_{c-a} = \frac{T_c \max - T_a}{P_d} \text{ (}^\circ\text{C/W)}$$

$T_c \max$ : Hybrid IC case temperature ( $^\circ\text{C}$ )

$T_a$ : Ambient temperature within the set ( $^\circ\text{C}$ )

$P_d$ : Average internal power dissipation within the hybrid IC (W)

As an example, figure 2 can be used to derive the required area for a 2 mm aluminum plate heat sink. Since the ambient temperature within a set varies greatly with the set internal air circulation conditions, the size of the heat sink must be determined taking into account the constraint that the temperature of the back surface of the IC (the aluminum plate side) must never under any conditions exceed  $105^\circ\text{C}$ .

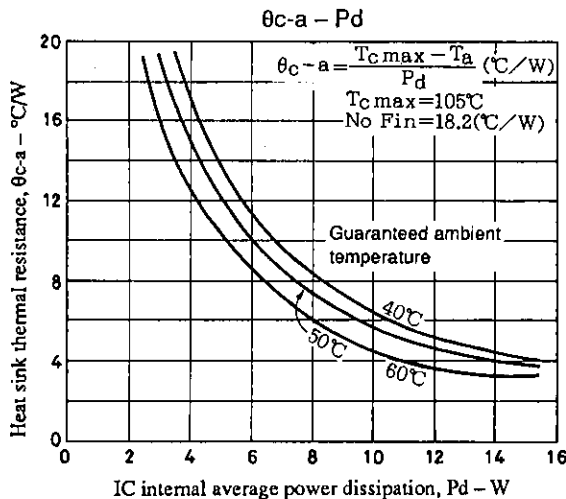


Figure 1  $\theta_{c-a}$  vs.  $P_d$

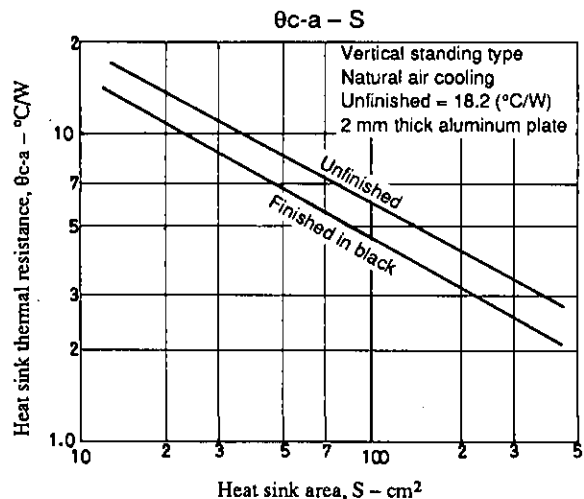


Figure 2  $\theta_{c-a}$  vs.  $S$

2. Hybrid IC Internal Average Power Dissipation (Pd)

Of the power dissipations within the hybrid IC, the following components have large power dissipations: the FETs that are the upper PWM elements in the H bridge structure, the lower FETs that form the motor direction reversing loop, and the flywheel FET body diode. This can be expressed as shown below from experiment (from the output current waveform in the figure below).

$$P_d = \text{upper FETs} + \text{lower FETs} + \text{body diode losses}$$

$$= V_{st} \times I_M \times f_p \times t_{ON} + V_{st} \times I_M + V_{df} \times I_M \times f_p \times t_{OFF}$$

- Vst: FET saturation voltage (V)
- I<sub>M</sub>: Motor output current (A)
- Vdf: The FET body diode forward voltage (V)
- f<sub>p</sub>: Chopping frequency (Hz)

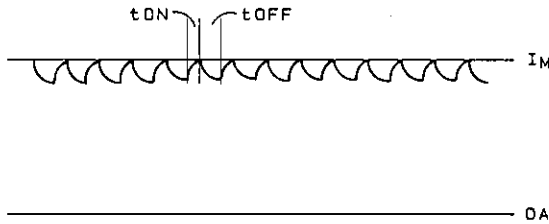


Figure 3 I<sub>M</sub> Waveform Model

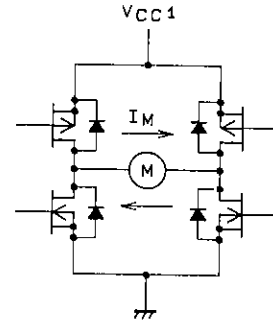


Figure 4 Model Circuit Diagram

Figures 5 and 6 show the I<sub>O</sub> vs. V<sub>st</sub> and I<sub>O</sub> vs. V<sub>df</sub> characteristics.

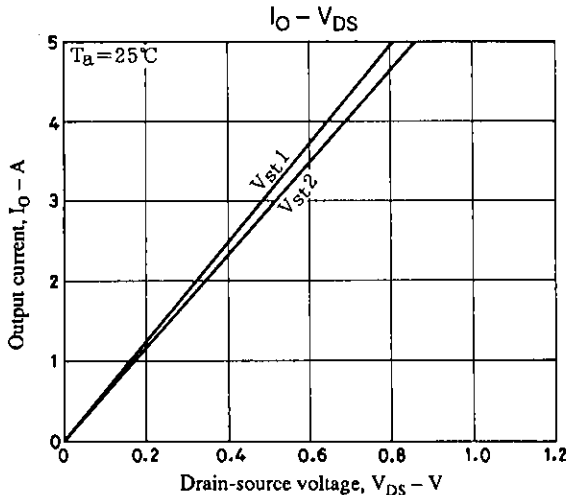


Figure 5 I<sub>O</sub> vs. V<sub>st</sub>

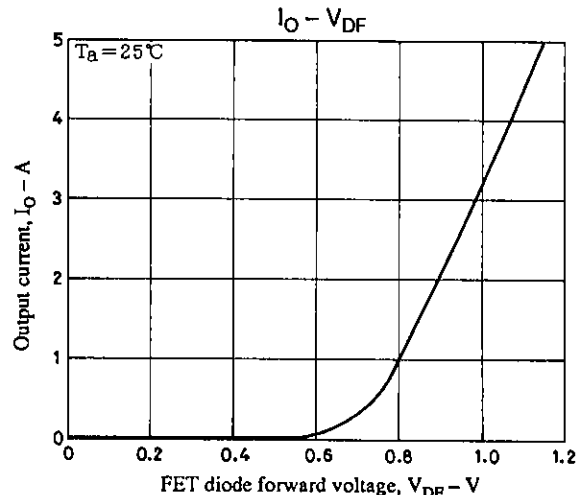


Figure 6 I<sub>O</sub> vs. V<sub>DF</sub>

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### 3. Junction Temperature, T<sub>j</sub>

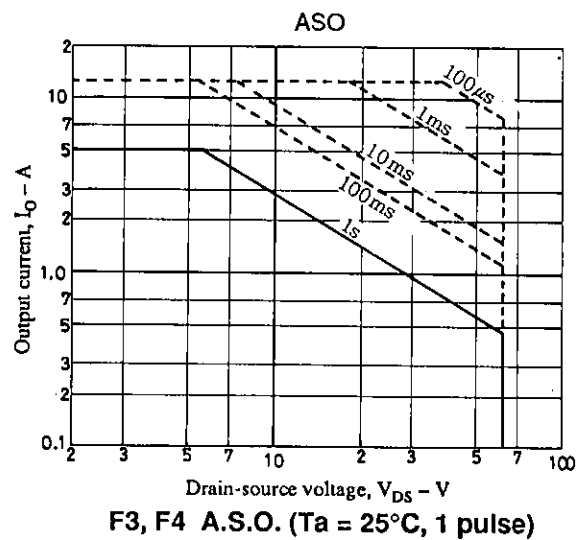
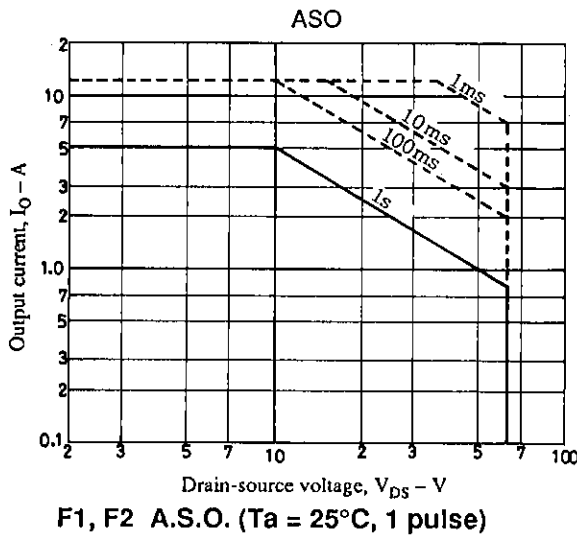
The junction temperatures T<sub>j</sub> (°C) for each element (F1, F2, F3 and F4) can be derived from the formula below from the power dissipation P<sub>ds</sub> (W) for each element and the junction thermal resistances θ<sub>j-c</sub> (°C/W).

$$T_j = T_c + \theta_{j-c} \times P_{ds} \text{ (}^\circ\text{C)}$$

P<sub>ds</sub> is the power dissipation per element. Note that the thermal resistances for the power elements are as follows.

F1, F2 θ<sub>j-c</sub> = 4 (°C/W)

F3, F4 θ<sub>j-c</sub> = 7 (°C/W)



## Usage Notes

### 1. Drive Circuit Startup Procedure

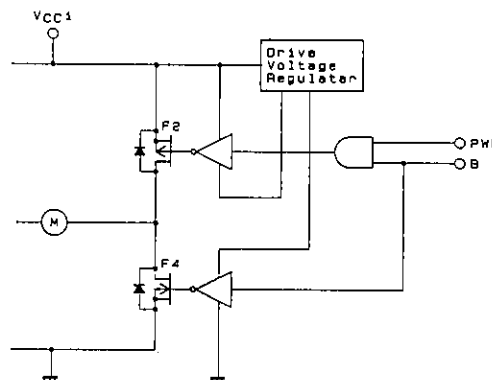


Figure 7 Upper and Lower MOSFET Drive Circuits

When starting (applying power to) the driver circuit (STK6855), the external control signals must be set to standby mode, i.e., pins A and B both set to low (setting both these pins high is an illegal mode). Then, after the specified power supply voltages (V<sub>CC1</sub> and V<sub>CC2</sub>) have been input to the driver circuit, the circuit can be driven by inputting external control signals.

2. Braking Operation Procedures

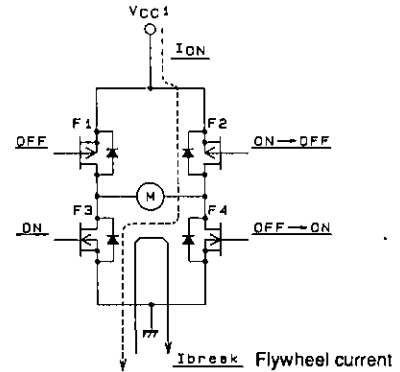
There are three methods for applying braking to the motor.

- (a) Setting both the A and B phase inputs to low. (This shorts the motor pins.)
- (b) Setting the PWM input low. (This effects motor flywheel current regenerative braking.)
- (c) After setting the PWM input low, setting both the A and B phase inputs to low. (This is the combination of methods (a) and (b).)

(a) When braking method (a) is used, damping is applied through the lower MOSFETs. (This stops the motor quickly.) Since this method is equivalent to shorting the motor, the braking flywheel current rises radically, and the lower MOSFETs goes to the overload state. As shown in figure 8, F3 and F4 go to the overload state, and figure 9 shows the flywheel current that flows in this braking method. Thus if this method is to be used, the user must confirm that, under the conditions of the actual application circuit, the flywheel current that flows in the lower FETs does not exceed the maximum rated current range for the hybrid IC.

When brake method (b) is used, the motor drive current from before braking is applied is released in the lower MOSFETS thus resulting in a motor stopping operation. (This is a free running motor stop method.) Although the MOSFETS will not be overloaded, the braking is not as fast.

When brake method (c) is used, first the PWM input is set to low, and the motor's rotational energy is released to a certain degree. Then full braking is applied by setting both the A and B phase inputs to low. This method allows the flywheel current that flows in the lower MOSFETS to be held to within the maximum rated range by first applying method (b) braking, and then when the motor's rotational energy has been reduced, applying method (a) braking to stop the motor.



Note: (\*) Braking applied during reverse motor rotation

Figure 8 Brake Method (a) Current Flow

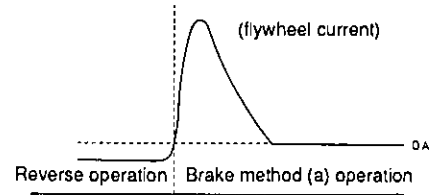
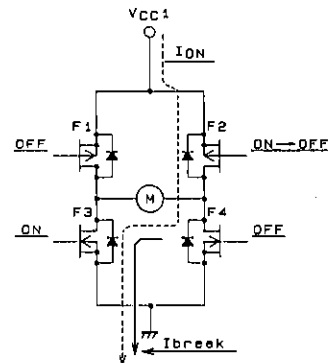


Figure 9 Flywheel Current Flowing In the Lower FET (F4)



Note: (\*) Braking applied during reverse motor rotation

Figure 10 Current Path In Brake Method (a)

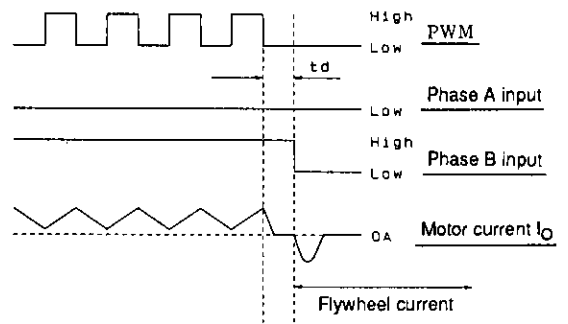
The dead time ( $t_d$ ) and the flywheel current must be checked with the motor actually used, since the amount of dead time ( $t_d$ ) that must be inserted between setting the PWM input low and setting the A and B phase inputs low to assure that the flywheel current is held within the maximum rated range will vary with the conditions under which the circuit operates. (See figure 11.)

Method (c) allows the motor to be stopped in a much shorter time than is possible with method (b). When releasing the brake it does not matter if the phase input signals or the PWM input signal is set to high first.

Although we have presented three braking methods, we recommend the use of method (c) due to the speed of braking and the current levels flowing during the braking operation.

3. Upper and Lower MOSFET Shorting Currents

It is conceivable that both the upper and lower MOSFETs could be in the on state at the same time during braking operations (braking methods (a) and (c)) and release states. Taking this into consideration, the STK6855 provides two dead times ( $t_{d1}$  and  $t_{d2}$ ) of at least  $1 \mu s$  with respect to the input signals in the upper and lower MOSFET drive circuits as shown in the figure below. As a result there is no need for concern about shorting currents in the upper and lower MOSFETs.



Note: (\*) Braking applied during reverse motor rotation

Figure 11 Input Signal Timing Chart for Braking Method (c)

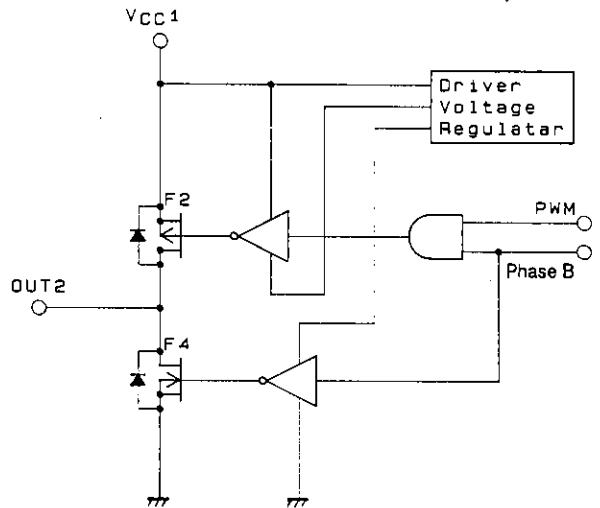
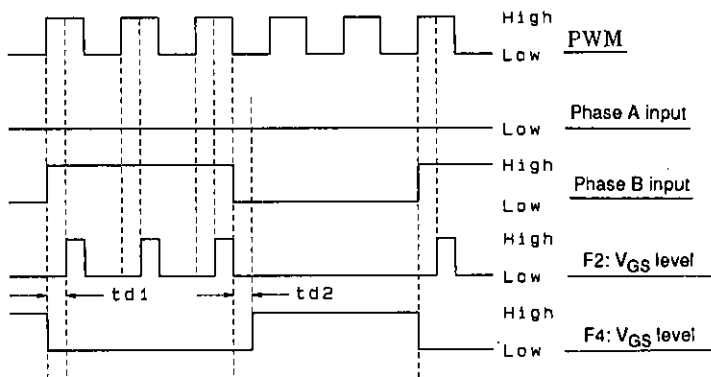


Figure 12 Upper and Lower MOSFET Equivalent Circuit



Note:  $t_{d1}$ : Dead time in the upper MOSFET drive circuit  
 $t_{d2}$ : Dead time in the lower MOSFET drive circuit  
 (\*)  $t_{d1}, t_{d2} \geq 1 \mu s$

Figure 13 Upper and Lower MOSFET  $V_{GS}$  Voltage Timing Chart